WEJ®

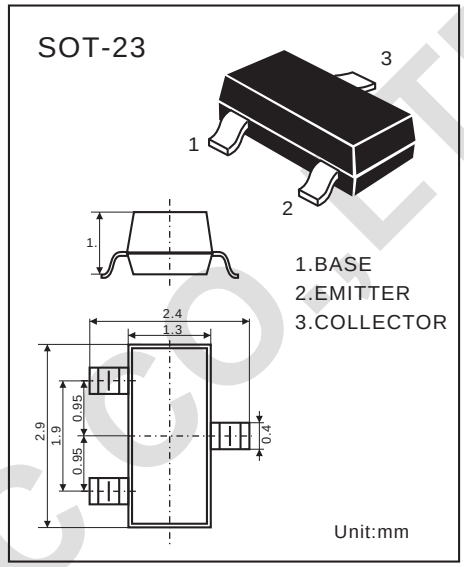
RoHS

2SC3734LT1

NPN EPITAXIAL SILICON TRANSISTOR

AM/FM IF AMPLIFIER,LOCAL OSCILATOR OF FM/VHF TUNER

- High Current Gain Bandwidth Product f_T=1100MHz



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	Ic	50	mA
Collector Dissipation Ta=25°C*	P_D	225	mW
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	-55~150	°C

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Condition
Collector-Base Breakdown Voltage	BV_{CBO}	30			V	I_C=100μA I_E=0
Collector-Emitter Breakdown Voltage#	BV_{CEO}	15			V	I_C=1mA I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E=100μA I_C=0
Collector-Base Cutoff Current	I_{CBO}			50	nA	V_{CB}=12V, V_E=0
Emitter-Base Cutoff Current	I_{EBO}			50	nA	V_{CB}=3V, I_C=0
DC Current Gain	H_{FE}	28	100	300		V_{CB}=5V, I_C=1mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5	V	I_C=10mA, I_B=1mA
Collector-Base Capacitance	C_{ob}		1.3	1.7	PF	V_{CB}=10V, I_E=10,f=1MHz
Collector-Gain-Bandwidth Product	f_T	700	1100		MHz	V_{CE}=5V, I_C=5mA

*Total Device Dissipation:FR=1X0.75X0.062 in Board Derate 25°C

#Pulse Test: Pulse Width 300uS Duty cycle 2%

DEVICE MARKING:

2SC3734LT1=J8